

at least one bridge arranged between said first and said second semiconductor chip and electrically connecting them;

external connecting electrodes provided to surround areas where said first and said second semiconductor chip are located, at least a portion of the rear surface of them serving as an electrode to be externally connected;

first metallic wires which electrically connect said first and said second semiconductor chip to said external connecting electrodes, respectively;

second metallic wires which electrically connect said first semiconductor chip, said bridge and said second semiconductor chip; and

insulating resin which seals said first and said second semiconductor chip, said external connecting electrode, and said first and said second metallic wires,

wherein said insulating resin separates said first and second die pad, said bridge and said external connecting electrodes from one another, and said second metallic wires are coupled to said first and said second semiconductor chip using a ball bond and coupled to said bridge using a stitch bond,

further comprising a plurality of recesses in a rear surface of said insulating resin, the rear surface of said first and second die pad and said external connecting electrodes being exposed within said recesses.

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10. (Amended) A semiconductor device comprising:

a first and a second semiconductor chip which are superposed on each other;

a first die pad to which said first semiconductor chip at a lower layer is fixed;

at least one bridge arranged between said first and said second semiconductor chip and electrically connecting them;

external connecting electrodes provided to surround areas where said first and said second semiconductor chip are located, at least a portion of the rear surface of them serving as an electrode to be externally connected;

first metallic wires which electrically connect said first and said second semiconductor chip to said external connecting electrodes, respectively;

second metallic wires which electrically connect said first semiconductor chip,  
said bridge and said second semiconductor chip; and

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insulating resin which seals said first and said second semiconductor chip, said  
external connecting electrode, and said first and said second metallic wires,

wherein said insulating resin exposes the rear surface of each of said bridge and  
said external connecting electrodes, and said second metallic wires are coupled to said first and  
said second semiconductor chip using a ball bond and coupled to said bridge using a stitch bond,

further comprising a plurality of recesses in a rear surface of said insulating resin,  
the rear surface of said first and second die pad and said external connecting electrodes being  
exposed within said recesses.

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Please add claims 22 - 27.

---22. (New) The semiconductor device according to claim 4, wherein said recess is  
formed by an insulating film coated on the rear surface of said insulating resin, said first and said  
second die pad and said bridge.--

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--23. (New) The semiconductor device according to claim 4, wherein said recesses are  
formed by a portion of the rear surface of said insulating resin of which a back surface protrudes  
from the rear surface of said first and said second die pad and said external connecting  
electrodes.--

*24*  
(--24) (New) The semiconductor device according to claim 10, wherein said recesses are  
formed by an insulating film coated on the rear surface of said insulating resin, said first die pad  
and said bridge.--

--25. (New) The semiconductor device according to claim 10, wherein said recesses are  
formed by a portion of the rear surface of said insulating resin of which a back surface protrudes  
from the rear surface of said first and second die pad and said external connecting electrodes.--

--26. (New) A semiconductor device comprising:

a first and a second semiconductor chip which are electrically connected to each other;

a first die pad to which said first semiconductor chip is fixed;

a second die pad to which said second semiconductor chip is fixed;

at least one bridge arranged between said first and said second semiconductor chip and electrically connecting them;

external connecting electrodes provided to surround areas where said first and said second semiconductor chip are located, at least a portion of the rear surface of them serving as an electrode to be externally connected;

first metallic wires which electrically connect said first and said second semiconductor chip to said external connecting electrodes, respectively

second metallic wires which electrically connect said first semiconductor chip, said bridge and said second semiconductor chip; and

insulating resin which seals said first and said second semiconductor chip, said external connecting electrode, and said first and said second metallic wires,

wherein said insulating resin separates said first and second die pad, said bridge and said external connecting electrodes from one another, and said second metallic wires are coupled to said first and said second semiconductor chip using a ball bond and coupled to said bridge using a stitch bond,

further comprising a plurality of recesses in a rear surface of said insulating resin, the rear surface of said first and second die pad and said external connecting electrodes being exposed within said recesses, wherein said recesses are formed by coating an insulating film on another part of the rear surface of said insulating resin, said first and said second die pad and said bridge, each area of said recesses being substantially the same size.--

--27. (New) A semiconductor device comprising:

a first and a second semiconductor chip which are superposed on each other;

a first die pad to which said first semiconductor chip at a lower layer is fixed;

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at least one bridge arranged between said first and said second semiconductor chip and electrically connecting them;

external connecting electrodes provided to surround areas where said first and said second semiconductor chip are located, at least a portion of the rear surface of them serving as an electrode to be externally connected;

first metallic wires which electrically connect said first and said second semiconductor chip to said external connecting electrodes, respectively

second metallic wires which electrically connect said first semiconductor chip, said bridge and said second semiconductor chip; and

insulating resin which seals said first and said second semiconductor chip, said external connecting electrode, and said first and said second metallic wires,

wherein said insulating resin exposes the rear surface of said bridge and said external connecting electrodes from one another, and said second metallic wires are coupled to said first using a ball bond and said second semiconductor chip and coupled to said bridge using a stitch bond,

further comprising a plurality of recesses in a rear surface of said insulating resin, the rear surface of said first and second die pad and said external connecting electrodes being exposed within said recesses, wherein the recesses are formed by coating an insulating film on another part of the rear surface of said insulating resin, said first die pad, each area of said recesses having substantially the same size.--

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In the drawings:

Please substitute drawing sheets labeled FIG. 1A, 2A, 3A, 4A, 6, 7, 11, and 12 with the respective corrected drawing sheets provided herein.